

• General Description

The TF015N03N uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

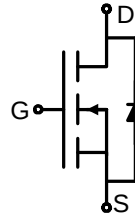
• Features

- Advance device constructure
- Low $R_{DS(ON)}$ to minimize conduction loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

Synchronous Rectification for AC-DC/DC-DC converter
Power Tools

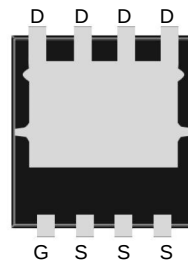
• Product Summary



$$V_{DS}=30V \quad I_D=165A$$

$$R_{DS(ON)}(10V \text{ typ})=1.5m\Omega$$

$$R_{DS(ON)}(4.5V \text{ typ})=2.3m\Omega$$



PDFN5x6-8L

• Package Marking and Ordering Information:

Part NO.	TF015N03N
Marking1	015N03N
Marking2	TF:tuofeng; Y:year code; X:Week; AA:device code;
Basic ordering unit	5000 / PCS

• Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	165	A
	$I_{D@TC=75^\circ C}$	115	A
	$I_{D@TC=100^\circ C}$	99	A
Pulsed Drain Current ①	I_{DM}	495	A
Total Power Dissipation	$P_D@TC=25^\circ C$	65	W
Total Power Dissipation	$P_D@TA=25^\circ C$	2.0	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	780	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	2.5	° C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	40	° C/W
Soldering temperature, wavesoldering for 8 s	T_{sold}	-	-	265	° C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	-	-	V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.1	1.5	2.1	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	-	1.5	2.0	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	2.3	3.0	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=25V, I_D=30A$	-	20	-	S
Source-drain voltage	V_{SD}	$I_S=20A$	-	0.78	1.20	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	$f = 1MHz$	-	7710	-	pF
Output capacitance	C_{oss}	$V_{DS}=30V$	-	845	-	
Reverse transfer capacitance	C_{rss}	$V_{GS}=0V$	-	838	-	
Turn-On Delay Time	$t_d(on)$	$V_{DS}=30V$	-	18	-	ns
Turn-On Rise Time	t_r	$V_{GS}=10V$	-	10	-	
Turn-Off Delay Time	$t_d(off)$	$I_D=30A$	-	64	-	
Turn-Off Fall Time	t_f	$R_g=1.8\Omega$	-	16	-	

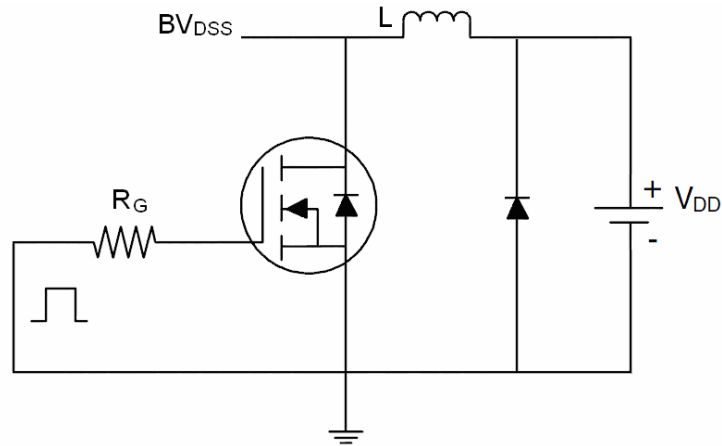
●Gate Charge characteristics($T_a = 25^\circ C$)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	$V_{DD}=30V$	-	142	-	nC
Gate - Source charge	Q_{gs}	$I_D=30A$	-	92	-	
Gate - Drain charge	Q_{gd}	$V_{GS}=10V$	-	18	-	

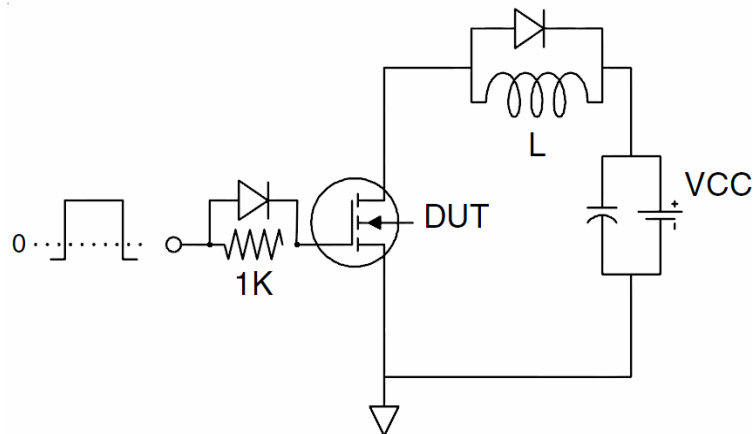
Note: ① Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$;

Test Circuit

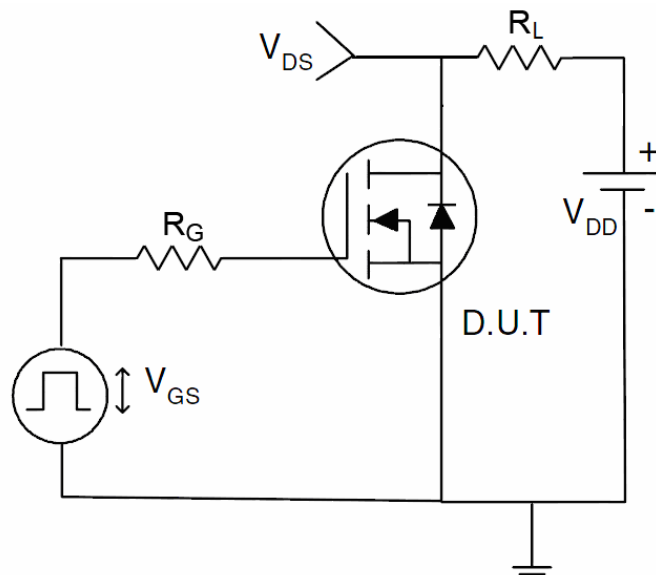
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

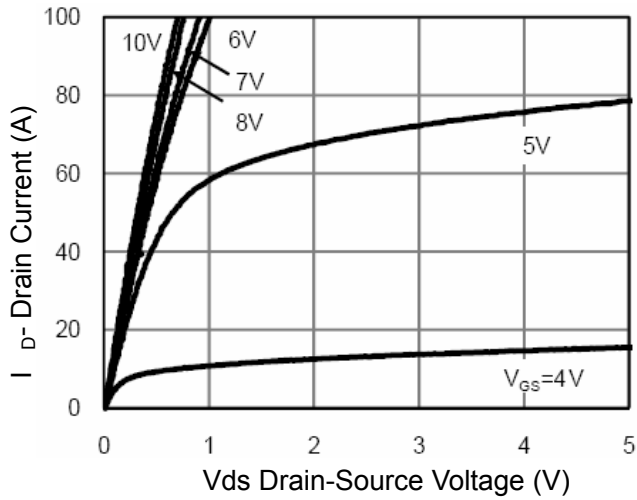


Figure 1 Output Characteristics

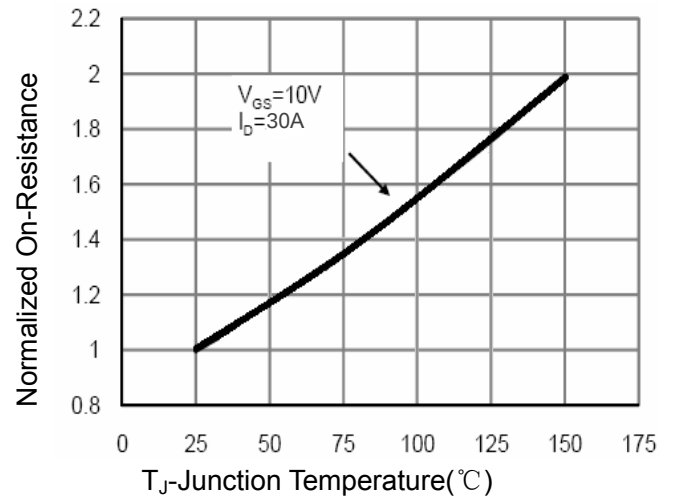


Figure 4 $R_{DS(on)}$ -Junction Temperature

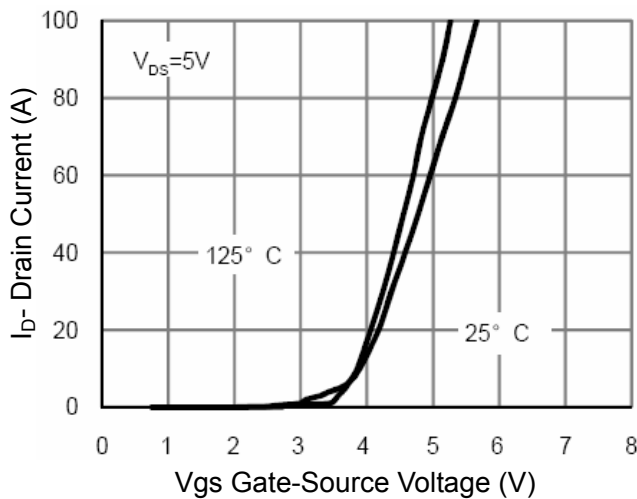


Figure 2 Transfer Characteristics

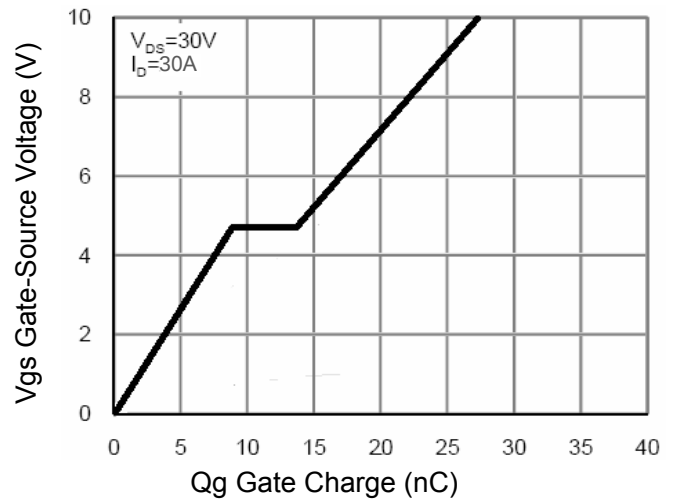


Figure 5 Gate Charge

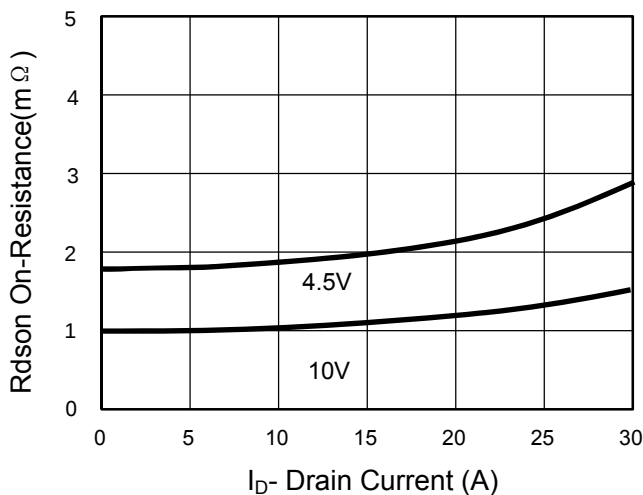


Figure 3 $R_{DS(on)}$ - Drain Current

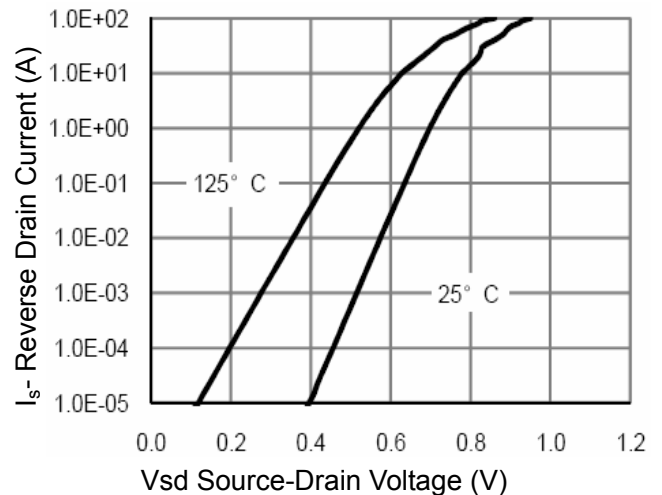


Figure 6 Source- Drain Diode Forward

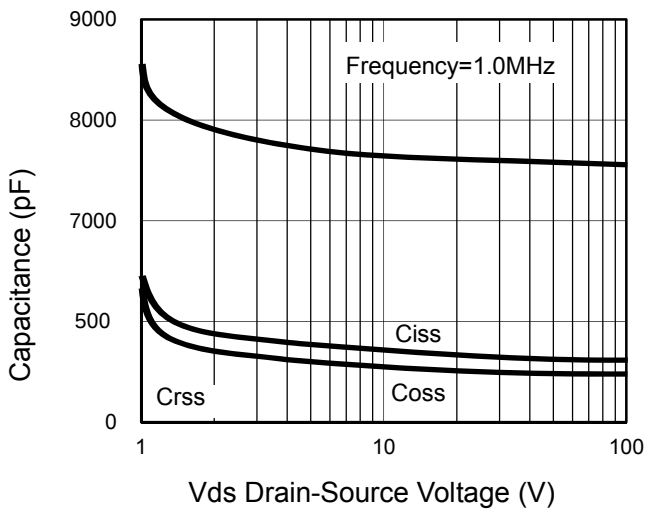


Figure 7 Capacitance vs Vds

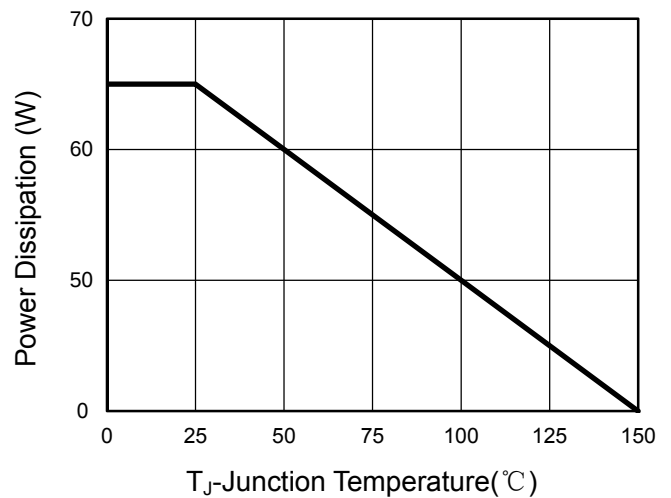


Figure 9 Power De-rating

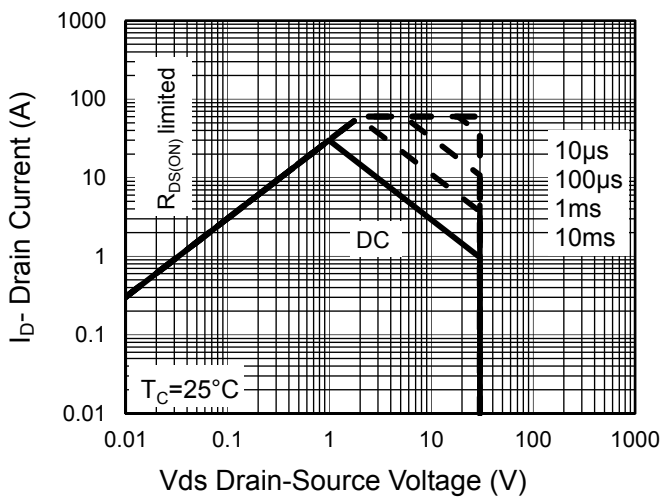


Figure 8 Safe Operation Area

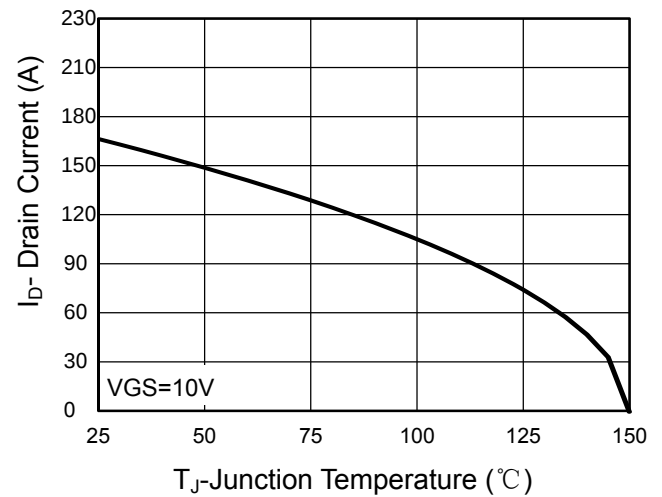


Figure 10 Current De-rating

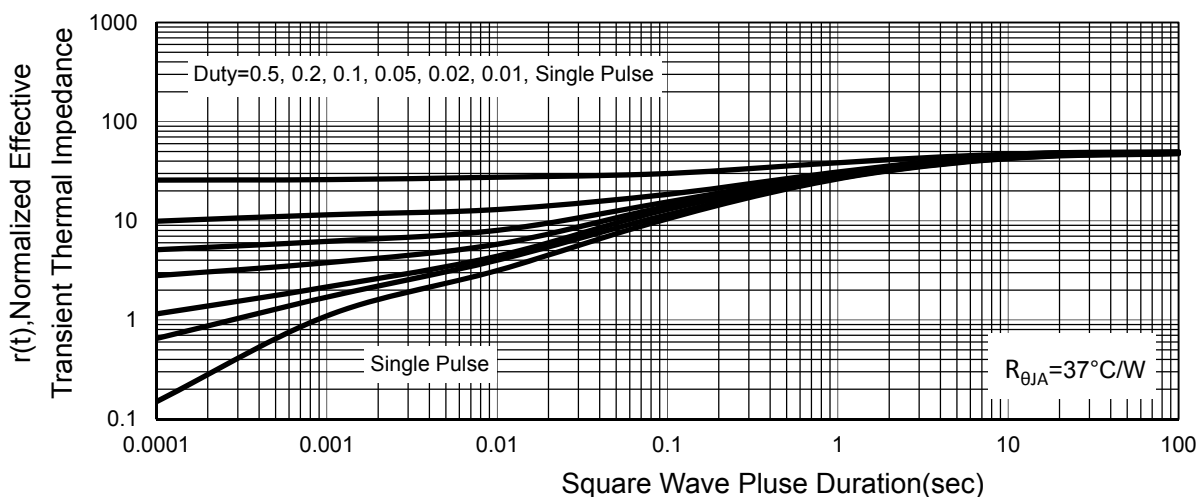
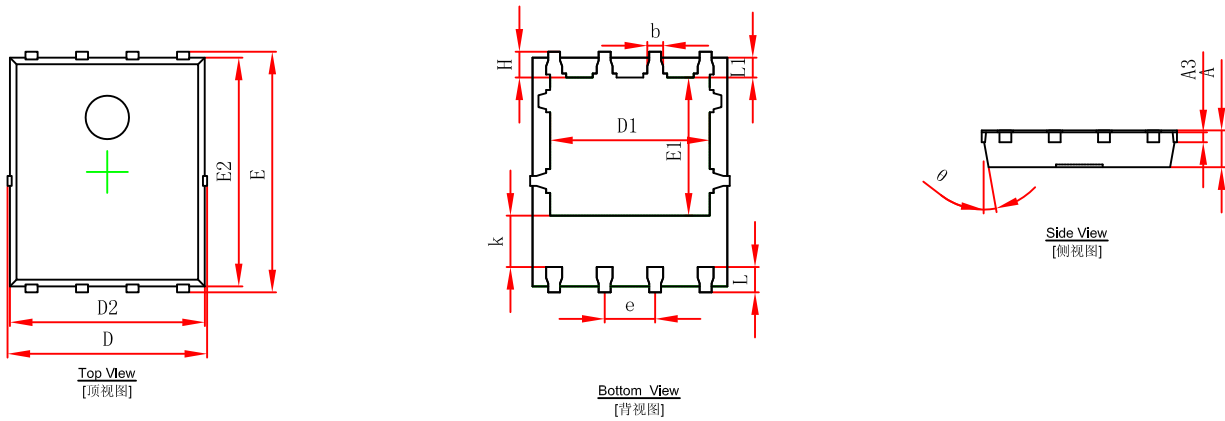


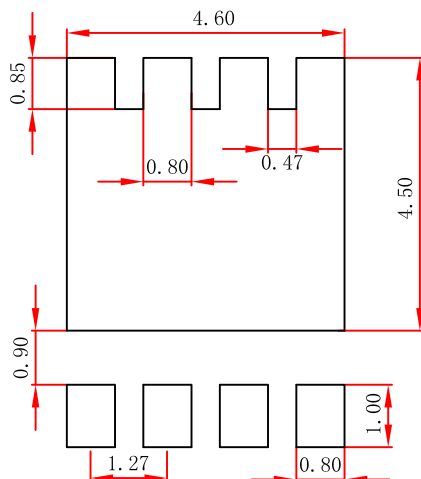
Figure 11 Normalized Maximum Transient Thermal Impedance

PDFN5x6-8L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A3	0.254REF.		0.010REF.	
D	4.944	5.200	0.195	0.205
E	5.974	6.200	0.235	0.244
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

PDFN5x6-8L Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.